Icemos Technology Ltd **Product Specification** **1000.743301** Issue Date 17 October 2023 10:3

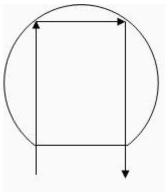
Part Number Customer

Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	100.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	{110} +/- 1.0 degree	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	None or SEMI Std	Wafer Vendor
	5.0	Overall Thickness	601.00 +/- 26.00 µm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process
	7.0	Bow	<60.00µm	ADE to ASTM F534, 100%
	8.0	Warp	<60.00µm	
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	{111} +/- 0.5 degree	Wafer Vendor
	13.0	Handle Thickness	475.00 +/- 25.00 µm	ADE, 100%
	14.0	Handle Doping Type	N	Wafer Vendor
	15.0	Handle Dopant	Any	Wafer Vendor
	16.0	Handle Resistivity	Any	Wafer Vendor
	17.0	Backside Finish	Lapped and etched with Oxide, and Lasermark	Guaranteed by process
BuriedOxide	18.0	Oxide Type	Thermal	
	19.0	Oxide Thickness	10,000.00 +/- 500.00 A	Nanospec centre point, 4%
	20.0	Oxide formed on	Handle and / or Device wafer	Graranteed by process
DeviceSilicon	21.0	Device Growth Method	CZ	Wafer Vendor
	22.0	Device Orientation	{111} +/- 0.5 degree	Wafer Vendor
	23.0	Nominal Thickness	125.00 +/- 1.00 µm	ADE, Single-point, 100%
	24.0	Distance to device silicon edge from wafer edge	<= 2mm	Guaranteed by process
	25.0	Device Doping Type	N	Wafer Vendor
	26.0	Device Dopant	Phos	Wafer Vendor
	27.0	Device Resistivity	0.003-0.01 Ohm-cm	Wafer Vendor
	28.0	Voids	none	Bright Light, 100% (note 2)
	29.0	Scratches	0	Bright Light, 100% (note 2)
	30.0	Haze	none	Bright Light, 100% (note 2)

Category	**Parameter**	**Specification**	**Measurement Method**
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

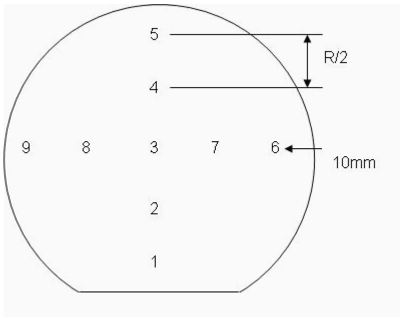
Explanatory Notes

1. Microscope inspection performed using microscope scan as below. 5x objective.



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information